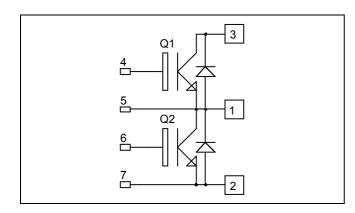


Phase leg Trench + Field Stop IGBT4 Power Module





Application

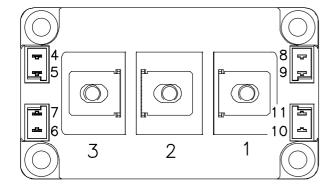
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
 - Kelvin emitter for easy drive
- High level of integration
- M6 power connectors



- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25$ °C	420	
	Continuous Conector Current	$T_C = 80$ °C	325	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1500	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
		$I_C = 300A$ $T_j = 125$ °C	$T_j = 125$ °C		2.2		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 11mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

	Characteristic	Test Conditions	r	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			18.6		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$	$V_{CE} = 25V$ f = 1MHz		1.16		
C_{res}	Reverse Transfer Capacitance	f = 1MHz			1		
Q_{G}	Gate charge	V_{GE} = -8V / 15V I_{C} =300A	V_{GE} = -8V / 15V ; V_{CE} =600V I_{C} =300A		1.7		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		200		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			40		
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 300 \text{A}$	$V_{CE} = 600V$ $V_{CE} = 300 A$		380		ns
$T_{\rm f}$	Fall Time	$R_G = 1.5\Omega$	-				
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 300A$ $R_{G} = 1.5\Omega$		220		ns
$T_{\rm r}$	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				450		
$T_{\rm f}$	Fall Time	$R_G = 1.5\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150$ °C		27		mJ
E _{off}	Turn-off Switching Energy	$I_C = 300A$ $R_G = 1.5\Omega$	$T_{J} = 150^{\circ}C$		29		mJ
I_{sc}	Short Circuit data		$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10 \mu s$; $T_j = 150 ^{\circ} C$		1200		A

Diode ratings and characteristics

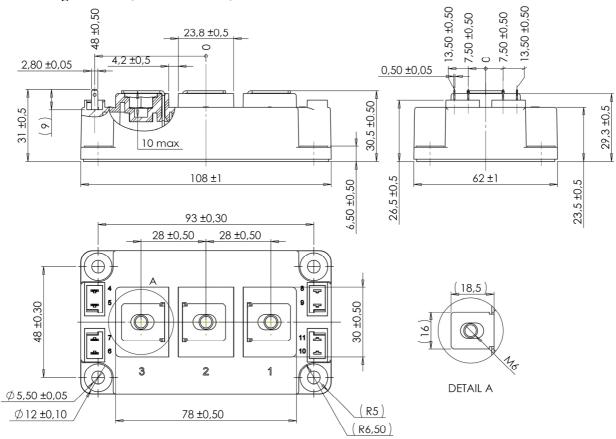
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 2000	μΑ
I_{F}	DC Forward Current		$T_{\rm C} = 80^{\circ} \rm C$		300	2000	A
N/	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.7	2.2	V
V_{F}			$T_{\rm j} = 150^{\circ}{\rm C}$		1.65		v
t	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$	$T_j = 25$ °C		155		ns
t _{rr}			$T_{j} = 150^{\circ}C$		300		
0	Payarga Pagayary Charga		$T_j = 25^{\circ}C$		29		μС
Q_{rr}	Reverse Recovery Charge	$di/dt = 7000A/\mu s$	$T_j = 150$ °C		61		
E_{rr}	Reverse Recovery Energy	·	$T_j = 25$ °C		13		mJ
L _{II}			$T_j = 150$ °C		24		1113



Thermal and package characteristics

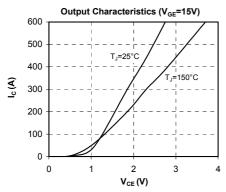
Symbol	Characteristic			Min	Тур	Max	Unit		
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.10	°C/W		
T _{th} JC			Diode			0.17	C/ W		
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V		
T_{J}	Operating junction temperature range			-40		175			
T_{STG}	Storage Temperature Range	-40 125 °C				°C			
$T_{\rm C}$	Operating Case Temperature			-40		125			
Torque	Mounting forque	For terminals	M6	3		5	N.m		
		To Heatsink	M6	3		5	11.111		
Wt	Package Weight					350	g		

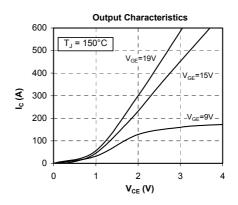
D3 Package outline (dimensions in mm)

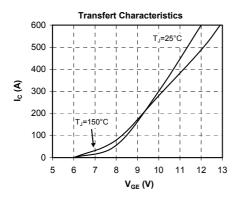


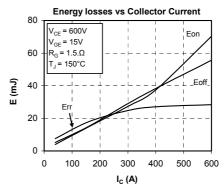


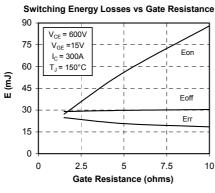
Typical Performance Curve

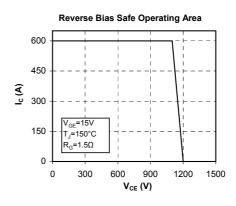


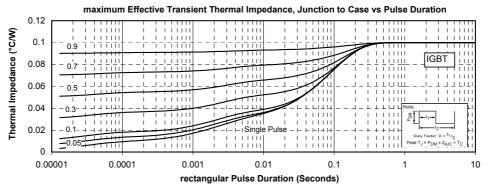




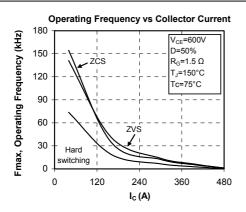


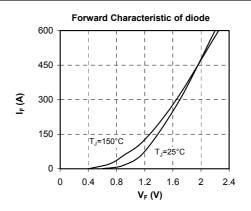


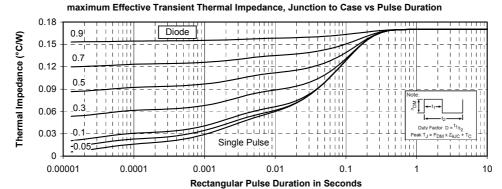














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